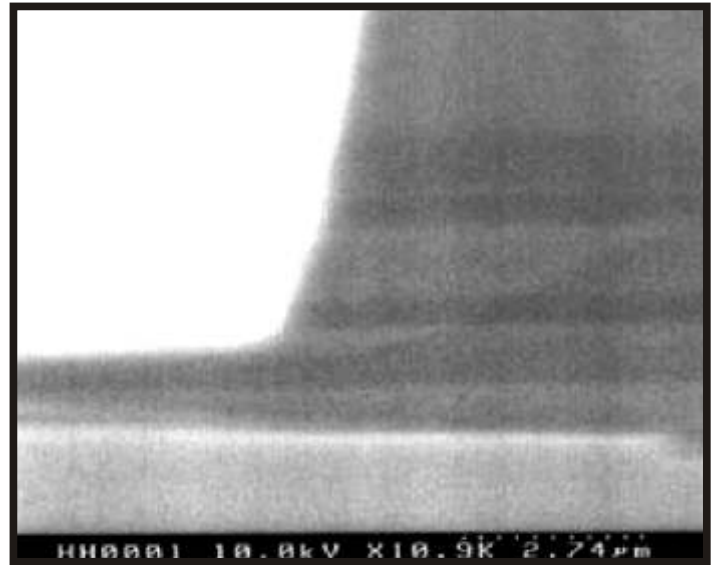
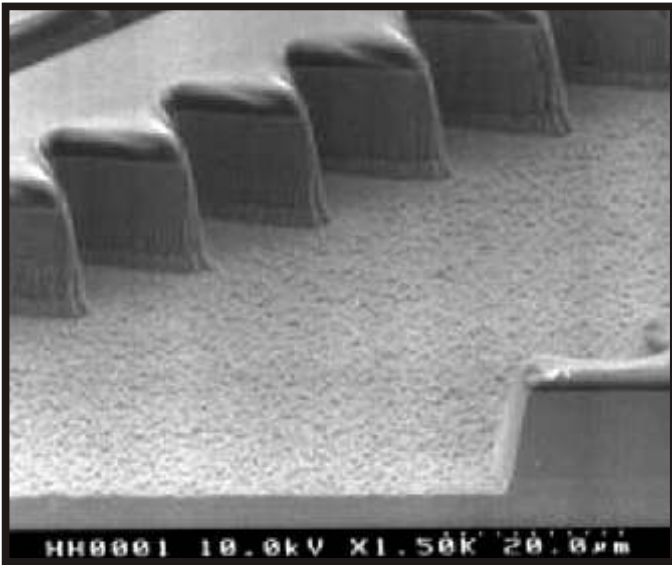


Plasmalab Data

$GaP/(Al_xGa_{(1-x)})_{0.5}In_{0.5}P/AlGaAs/GaAs$ - RIE with 70° walls



with kind permission
Dr. Daleiden
Head of III/V-Technology
Institute of Microstructure Technology and Analytics
Uni Kassel

Plasmalab 80 Plus

Plasmalab System 100

Plasmalab System 133



Technology:
RIE, 13.56 Mhz
Chlorine based process

Results:
15.8 µm deep etch
at the required 70° wall angle in 15 min
mask: 5.5 µm photoresist
selectivity: 4 : 1

